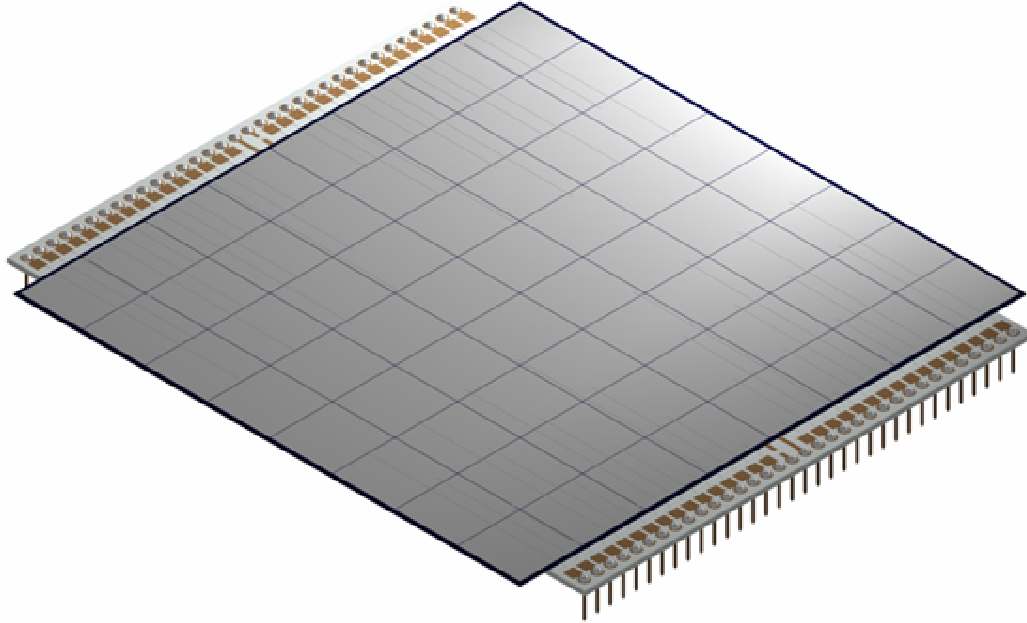


DESIGN MSPX SERIES CUSTOM SILICON PIXEL DETECTORS

SILICON DETECTOR TYPE: SINGLE SIDED DC PIXEL DETECTORS
 DESIGN: Totally depleted ion implanted structures.

MSPX080



SINGLE SIDED MSPX SERIES:

DESIGN	ACTIVE PIXEL AREA DIMENSION (μm^2)	PIXEL ARRAY	CHIP DIMENSIONS (mm^2)	WINDOW	GUARD RING DESIGN	WAFER TECHNOLOGY (inch)	PACKAGE
MSPX040	1400 x 1400	4 x 4	9.10 x 9.10	Standard	Multi	4	Chip Only
MSPX041	900 x 900	4 x 4	9.10 x 9.10	Standard	Multi	4	Chip Only
MSPX080	12075.0 x 12075.0	8 x 8	99.0 x 99.0	Standard	Multi	6	Chip Only or Ceramic
MSPX 100 x 64	89.0 x 39.0	100 x 64	14.5 x 15.0	Standard	Multi	4	Chip Only
MSPX 128 x 96	100.0 x 100.0	128 x 96	17.5 x 22.15	Standard	Multi	6	Chip Only

DESIGNATION EXAMPLE: MSX003-300
 SILICON THICKNESS

4 INCH WAFERS: 65, 140, 250, 300, 500 and 1000 μm
 6 INCH WAFERS: 200, 300 and 400 μm

RADIATION HARDNESS: Survival to 10^{14} Neutrons, 10^{15} Protons
 CAPACITANCE: Subject to depletion depth e.g. 40 pF/cm for 300 μm
 LEAKAGE CURRENT: 1 nA/cm to 8 nA/cm subject to active area and depletion depth.

QUALITY ASSURANCE :ISO9001

